

Preliminary

SIDC03D60F6

Fast switching diode chip in EMCON-Technology

FEATURES:

- 600V EMCON technology 70 µm chip
- soft , fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

EUPEC power modules and discrete devices



Applications:

SMPS, resonant applications, drives

Chip Type	V_R	I _F	Die Size	Package	Ordering Code
SIDC03D60F6	600V	6A	1.2 x 2.25 mm ²	sawn on foil	Q67050-A4037- A001

MECHANICAL PARAMETER:

Raster size	1.2 x 2.25				
Area total / active	2.7 / 1.45	mm ²			
Anode pad size	1.77 x 0.72	1			
Thickness	70				
Wafer size	150				
Flat position	180	deg			
Max. possible chips per wafer	5650 pcs				
Passivation frontside	Photoimide				
Anode metallisation	3200 nm AlSiCu				
Cathode metallisation	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding				
Die bond	electrically conductive glue or solder				
Wire bond	AI, ≤250μm				
Reject Ink Dot Size	Ø 0.65mm; max 1.2mm				
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C				



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Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}		600	V
Continuous forward current limited by T_{jmax}	I _F		6	
Single pulse forward current (depending on wire bond configuration)	I _{FSM}	$t_P = 10 \; ms \; sinusoidal$	tbd	А
Maximum repetitive forward current limited by T _{jmax} (depending on wire bond configuration)	I _{FRM}		12	
Operating junction and storage temperature	$T_{\rm j}$, $T_{ m stg}$		-55+150	°C

Static Electrical Characteristics (tested on chip), T_j =25 °C, unless otherwise specified

Parameter	Symbol	Condi	Value			Unit	
raiailletei	Syllibol	Conditions		min.	Тур.	max.	Joint
Reverse leakage current	I_{R}	V _R =600V	<i>T_j</i> =25 °C			250	μΑ
Cathode-Anode breakdown Voltage	V _{Br}	I _R =500μA	<i>T_j</i> =25°C	600			V
Forward voltage drop	V _F	I _F =6A	T _j =25°C		1.45		V

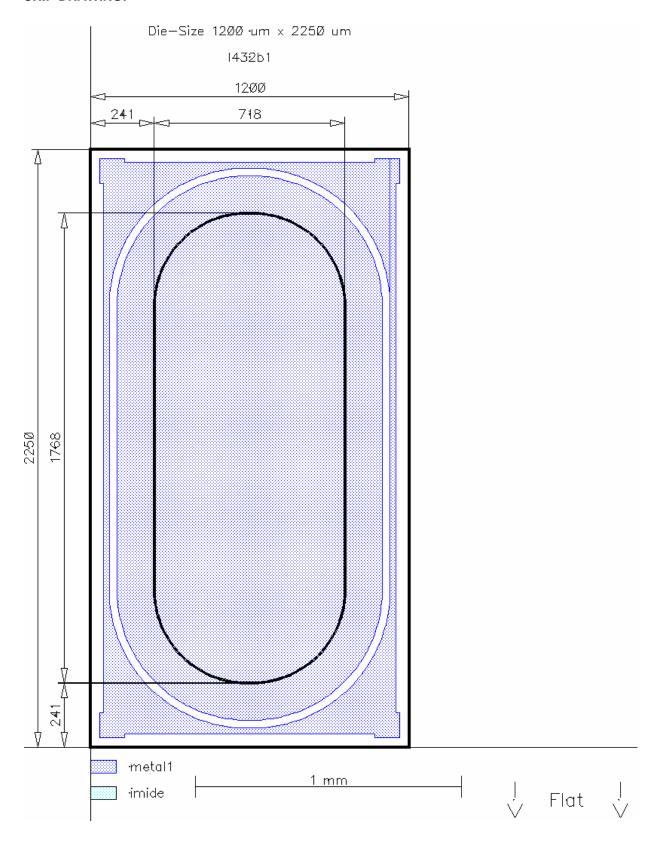
Dynamic Electrical Characteristics, at T_j = 25 °C, unless otherwise specified, tested at component

Parameter	Symbol	Conditions		Value			Unit
raidilletei	Syllibol			min.	Тур.	max.	Onn
Reverse recovery time	t _{rr1}	I _F =6A	$T_j = 25$ °C		70		
	t _{rr2}	$di/dt=550A/ms$ $V_R=400V$	$T_j = 150$ °C		105		ns
Peak recovery current	I _{RRM1}	$I_F=6A$	$T_j = 25$ °C		6.5		_
	I _{RRM2}	$\begin{array}{c c} \hline di/dt=550A/ms \\ V_R=400V \end{array}$	$T_j = 150$ °C		7.9		A
Reverse recovery charge	Q _{rr1}	I _F =6A di/dt=550A/ m s	T _j =25°C		240		nC
		$V_R = 400V$	T _j =150°C		400]''
Peak rate of fall of reverse	di _{rr1} /dt	I _F =6A	T _j =25°C		tbd		Λ/110
recovery current	di _{rr2} /dt	di/dt=550A/ms $V_R=400V$	T _j =150°C				A/μs
Softness	S1	IF=6A	<i>T_j</i> =25 °C		4		1
	S2	$\begin{array}{c} \text{di/dt=550A/ms} \\ V_{R} = 400 \text{V} \end{array}$	T _j =150°C		4.9		<u> </u>



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CHIP DRAWING:





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FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the	INFINEON TECHNOLOGIES /	tbd
device data sheet	EUPEC	tbu

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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